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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	138
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f723iet7

  - 1 x CAN (2.0B active)
  - 2 x SDMMCs
- Advanced connectivity
  - USB 2.0 full-speed device/host/OTG controller with on-chip PHY
  - USB 2.0 high-speed/full-speed device/host/OTG controller with dedicated DMA, on-chip full-speed PHY and on-chip Hi-speed PHY or ULPI depending on the part number
- True random number generator
- CRC calculation unit
- RTC: subsecond accuracy, hardware calendar
- 96-bit unique ID

Table 1. Device summary

Reference	Part number
STM32F722xx	STM32F722IE, STM32F722ZE, STM32F722VE, STM32F722RE, STM32F722IC, STM32F722ZC, STM32F722VC, STM32F722RC
STM32F723xx	STM32F723IE, STM32F723ZE, STM32F723VE, STM32F723IC, STM32F723ZC

2.13 Boot modes

At startup, the boot memory space is selected by the BOOT pin and BOOT_ADDx option bytes, allowing to program any boot memory address from 0x0000 0000 to 0x3FFF FFFF which includes:

- All Flash address space mapped on ITCM or AXIM interface
- All RAM address space: ITCM, DTCM RAMs and SRAMs mapped on AXIM interface
- The System memory bootloader

The boot loader is located in system memory. It is used to reprogram the Flash memory through a serial interface.

2.14 Power supply schemes

- V_{DD} = 1.7 to 3.6 V: external power supply for I/Os and the internal regulator (when enabled), provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 1.7 to 3.6 V: external analog power supplies for ADC, DAC, Reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.
- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

Note: The V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the internal reset is OFF (refer to Section 2.15.2: Internal reset OFF). Refer to Table 3: Voltage regulator configuration mode versus device operating mode to identify the packages supporting this option.

- The $V_{DDSDMMC}$ can be connected either to V_{DD} or an external independent power supply (1.8 to 3.6V) for the SDMMC2 pins (clock, command, and 4-bit data). For example, when the device is powered at 1.8V, an independent power supply 2.7V can be connected to $V_{DDSDMMC}$.When the $V_{DDSDMMC}$ is connected to a separated power supply, it is independent from V_{DD} or V_{DDA} but it must be the last supply to be provided and the first to disappear. The following conditions $V_{DDSDMMC}$ must be respected:
  - During the power-on phase (V_{DD} < V_{DD_MIN}), $V_{DDSDMMC}$ should be always lower than V_{DD}
  - During the power-down phase (V_{DD} < V_{DD_MIN}), $V_{DDSDMMC}$ should be always lower than V_{DD}
  - The $V_{DDSDMMC}$ rising and falling time rate specifications must be respected
  - In the operating mode phase, $V_{DDSDMMC}$ could be lower or higher than V_{DD}: All associated GPIOs powered by $V_{DDSDMMC}$ are operating between $V_{DDSDMMC\_MIN}$ and $V_{DDSDMMC\_MAX}$.
- The V_{DDUSB} can be connected either to V_{DD} or an external independent power supply (3.0 to 3.6V) for USB transceivers (refer to *Figure 7* and *Figure 8*). For example, when the device is powered at 1.8V, an independent power supply 3.3V can be connected to the V_{DDUSB}. When the V_{DDUSB} is connected to a separated power supply, it is independent from V_{DD} or V_{DDA} but it must be the last supply to be provided and the first to disappear. The following conditions V_{DDUSB} must be respected:
  - During the power-on phase (V_{DD} < V_{DD_MIN}), V_{DDUSB} should be always lower than V_{DD}
  - During the power-down phase (V_{DD} < V_{DD_MIN}), V_{DDUSB} should be always lower than V_{DD}

All the RTC events (Alarm, WakeUp Timer, Timestamp or Tamper) can generate an interrupt and wakeup the device from the low-power modes.

2.18 Low-power modes

The devices support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

  The Stop mode achieves the lowest power consumption while retaining the contents of SRAM and registers. All clocks in the 1.2 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled.

  The voltage regulator can be put either in main regulator mode (MR) or in low-power mode (LPR). Both modes can be configured as follows (see *Table 5: Voltage regulator modes in stop mode*):

  – Normal mode (default mode when MR or LPR is enabled)

  – Under-drive mode.

  The device can be woken up from the Stop mode by any of the EXTI line (the EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm / wakeup / tamper / time stamp events, the USB OTG FS/HS wakeup and the LPTIM1 asynchronous interrupt).

Table 5. Voltage regulator modes in stop mode

Voltage regulator configuration	Main regulator (MR)	Low-power regulator (LPR)
Normal mode	MR ON	LPR ON
Under-drive mode	MR in under-drive mode	LPR in under-drive mode

- **Standby mode**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.2 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

  The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising or falling edge on one of the 6 WKUP pins (PA0, PA2, PC1, PC13, PI8, PI11), or an RTC alarm / wakeup / tamper /time stamp event occurs.

  The Standby mode is not supported when the embedded voltage regulator is bypassed and the 1.2 V domain is controlled by an external power.

Table 10. STM32F722xx and STM32F723xx pin and ball definition

Pin Number										Pin name (function after reset)[1]	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32F722xx					STM32F723xx										
LQFP64	LQFP100	LQFP144	UFBGA176	LQFP176	WLCSP100	UFBGA176	UFBGA144	LQFP144	LQFP176						
-	1	1	A2	1	C9	A2	A3	1	1	PE2	I/O	FT	-	TRACECLK, SPI4_SCK, SAI1_MCLK_A, QUADSPI_BK1_IO2, FMC_A23, EVENTOUT	-
-	2	2	A1	2	A10	A1	A2	2	2	PE3	I/O	FT	-	TRACED0, SAI1_SD_B, FMC_A19, EVENTOUT	-
-	3	3	B1	3	D9	B1	B2	3	3	PE4	I/O	FT	-	TRACED1, SPI4_NSS, SAI1_FS_A, FMC_A20, EVENTOUT	-
-	4	4	B2	4	E8	B2	B3	4	4	PE5	I/O	FT	-	TRACED2, TIM9_CH1, SPI4_MISO, SAI1_SCK_A, FMC_A21, EVENTOUT	-
-	5	5	B3	5	B10	B3	B4	5	5	PE6	I/O	FT	-	TRACED3, TIM1_BKIN2, TIM9_CH2, SPI4_MOSI, SAI1_SD_A, SAI2_MCK_B, FMC_A22, EVENTOUT	-
1	6	6	C1	6	C10	C1	C2	6	6	VBAT	S	-	-	-	-

Table 12. STM32F722xx and STM32F723xx alternate function mapping

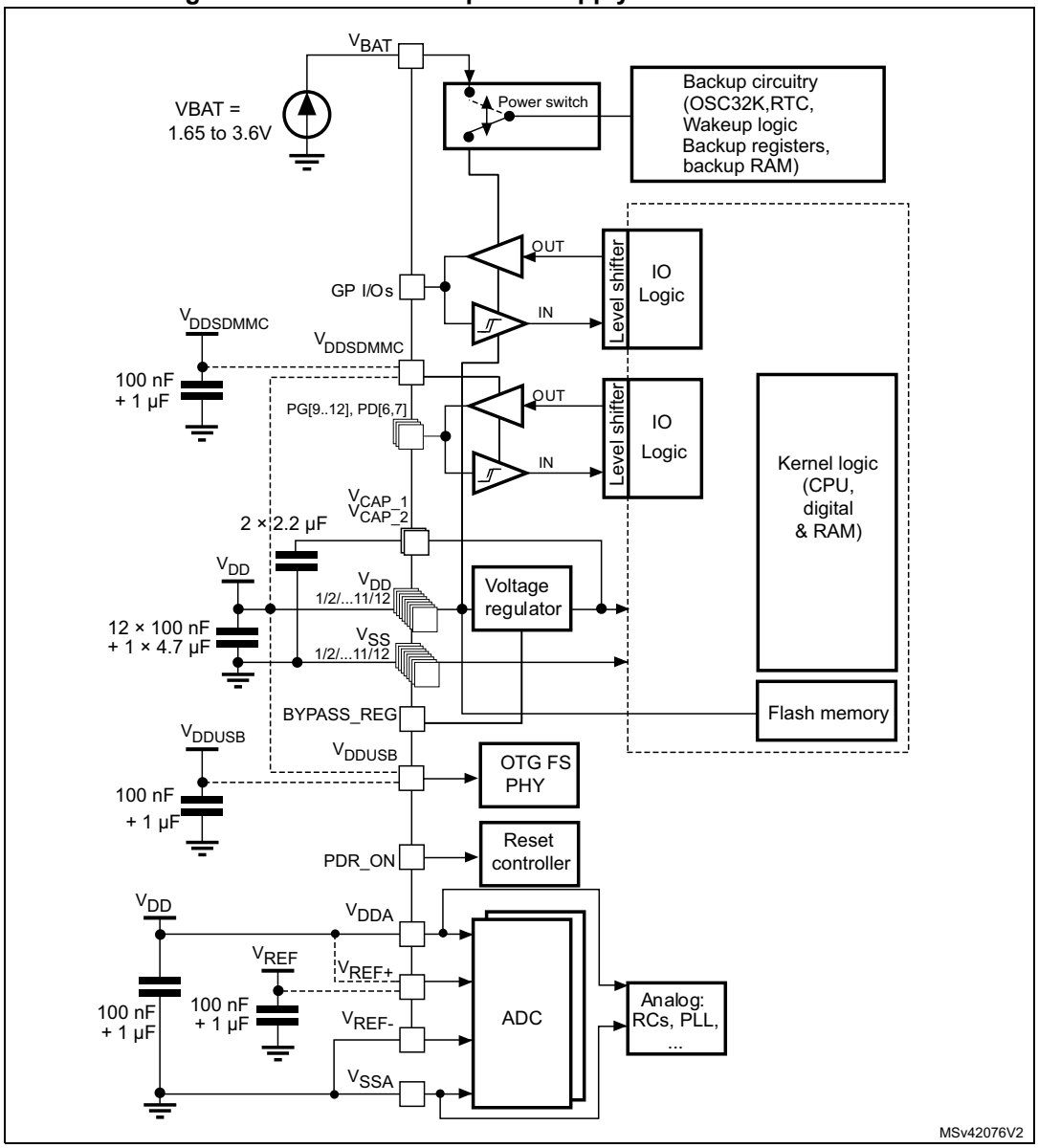
Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1	I2C1/2/3/USART1	SPI1/I2S1/SPI2/I2S2/SPI3/I2S3/SPI4/5	SPI2/I2S2/SPI3/I2S3/SPI3/I2S3/SAI1/UART4	SPI2/I2S2/SPI3/I2S3/USART1/2/3/UART5	SAI2/USART6/UART4/5/7/8/OTG1_FS	CAN1/TIM12/13/14/QUADSPI/FMC/OTG2_HS	SAI2/QUADSPI/SDMMC2/OTG2_HS/OTG1_FS	SDMMC2	UART7/FMC/SDMMC1/OTG2_FS	SYS
Port A	PA0	-	TIM2_CH1/TIM2_ETR	TIM5_CH1	TIM8_ETR	-	-	-	USART2_CTS	UART4_ TX	-	SAI2_SD_B	-	-	EVENTOUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_RTS	UART4_RX	QUADSPI_BK1_IO3	SAI2_MCK_B	-	-	EVENTOUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-	-	USART2_TX	SAI2_SCK_B	-	-	-	-	EVENTOUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-	-	USART2_RX	-	-	OTG_HS_ULPI_D0	-	-	EVENTOUT
	PA4	-	-	-	-	-	SPI1_NSS/I2S1_WS	SPI3_NSS/I2S3_WS	USART2_CK	-	-	-	-	OTG_HS_SOF	EVENTOUT
	PA5	-	TIM2_CH1/TIM2_ETR	-	TIM8_CH1N	-	SPI1_SCK/I2S1_CK	-	-	-	-	OTG_HS_ULPI_CK	-	-	EVENTOUT
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	-	-	TIM13_CH1	-	-	-	EVENTOUT
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI/I2S1_SD	-	-	-	TIM14_CH1	-	-	FMC_SDNWE	EVENTOUT
	PA8	MCO1	TIM1_CH1	-	TIM8_BKIN2	I2C3_SCL	-	-	USART1_CK	-	-	OTG_FS_SOF	-	-	EVENTOUT
	PA9	-	TIM1_CH2	-	-	I2C3_SMBA	SPI2_SCK/I2S2_CK	-	USART1_TX	-	-	-	-	-	EVENTOUT
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX	-	-	OTG_FS_ID	-	-	EVENTOUT
	PA11	-	TIM1_CH4	-	-	-	-	-	USART1_CTS	-	CAN1_RX	OTG_FS_DM	-	-	EVENTOUT

Table 12. STM32F722xx and STM32F723xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1	I2C1/2/3/USART1	SPI1/I2S1/SPI2/I2S2/SPI3/I2S3/SPI4/5	SPI2/I2S2/SPI3/I2S3/SPI3/I2S3/SAI1/UART4	SPI2/I2S2/SPI3/I2S3/USART1/2/3/UART5	SAI2/USART6/UART4/5/7/8/OTG1_FS	CAN1/TIM12/13/14/QUADSPI/FMC/OTG2_HS	SAI2/QUADSPI/SDMMC2/OTG2_HS/OTG1_FS	SDMMC2	UART7/FMC/SDMMC1/OTG2_FS	SYS
Port B	PB9	-	-	TIM4_CH4	TIM11_CH1	I2C1_SDA	SPI2_NSS/I2S2_WS	-	-	-	CAN1_TX	SDMMC2_D5	-	SDMMC1_D5	EVENTOUT
	PB10	-	TIM2_CH3	-	-	I2C2_SCL	SPI2_SCK/I2S2_CK	-	USART3_TX	-	-	OTG_HS_ULPI_D3	-	-	EVENTOUT
	PB11	-	TIM2_CH4	-	-	I2C2_SDA	-	-	USART3_RX	-	-	OTG_HS_ULPI_D4	-	-	EVENTOUT
	PB12	-	TIM1_BKIN	-	-	I2C2_SMBA	SPI2_NSS/I2S2_WS	-	USART3_CK	-	-	OTG_HS_ULPI_D5	-	OTG_HS_ID	EVENTOUT
	PB13	-	TIM1_CH1N	-	-	-	SPI2_SCK/I2S2_CK	-	USART3_CTS	-	-	OTG_HS_ULPI_D6	-	-	EVENTOUT
	PB14	-	TIM1_CH2N	-	TIM8_CH2N	-	SPI2_MISO	-	USART3_RTS	-	TIM12_CH1	SDMMC2_D0	-	OTG_HS_DM	EVENTOUT
	PB15	RTC_REFIN	TIM1_CH3N	-	TIM8_CH3N	-	SPI2_MOSI/I2S2_SD	-	-	-	TIM12_CH2	SDMMC2_D1	-	OTG_HS_DP	EVENTOUT
Port C	PC0	-	-	-	-	-	-	-	-	SAI2_FS_B	-	OTG_HS_ULPI_STP	-	FMC_SDNWE	EVENTOUT
	PC1	TRACED0	-	-	-	-	SPI2_MOSI/I2S2_SD	SAI1_SD_A	-	-	-	-	-	-	EVENTOUT
	PC2	-	-	-	-	-	SPI2_MISO	-	-	-	-	OTG_HS_ULPI_DIR	-	FMC_SDNE0	EVENTOUT
	PC3	-	-	-	-	-	SPI2_MOSI/I2S2_SD	-	-	-	-	OTG_HS_ULPI_NXT	-	FMC_SDCKE0	EVENTOUT

5.1.6 Power supply scheme

Figure 27. STM32F722xx power supply scheme



1. The two 2.2 µF ceramic capacitors should be replaced by two 100 nF decoupling capacitors when the voltage regulator is OFF.
2. The 4.7 µF ceramic capacitor must be connected to one of the V_{DD} pin.
3. $V_{DDA}=V_{DD}$ and $V_{SSA}=V_{SS}$.

Table 16. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	− 65 to +150	°C
T_J	Maximum junction temperature	125	

5.3 Operating conditions

5.3.1 General operating conditions

Table 17. General operating conditions

Symbol	Parameter	Conditions[1]		Min	Typ	Max	Unit
f_{HCLK}	Internal AHB clock frequency	Power Scale 3 (VOS[1:0] bits in PWR_CR register = 0x01), Regulator ON, over-drive OFF		0	-	144	MHz
		Power Scale 2 (VOS[1:0] bits in PWR_CR register = 0x10), Regulator ON	Over-drive OFF	0	-	168	
			Over-drive ON		-	180	
		Power Scale 1 (VOS[1:0] bits in PWR_CR register= 0x11), Regulator ON	Over-drive OFF	0	-	180	
			Over-drive ON		-	216[2]	
f_{PCLK1}	Internal APB1 clock frequency	Over-drive OFF		0	-	45	
		Over-drive ON		0	-	54	
f_{PCLK2}	Internal APB2 clock frequency	Over-drive OFF		0	-	90	
		Over-drive ON		0	-	108	
V_{DD}	Standard operating voltage	-		1.7[3]	-	3.6	V
V_{DDA}[4][5]	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as V_{DD}[6]		1.7[3]	-	2.4	
	Analog operating voltage (ADC limited to 2.4 M samples)			2.4	-	3.6	
V_{DDUSB}	USB supply voltage (supply voltage for PA11,PA12, PB14 and PB15 pins)	USB not used		1.7	3.3	3.6	
		USB used		3.0	-	3.6	
V_{BAT}	Backup operating voltage	-		1.65	-	3.6	
$V_{DDSDMMC}$	SDMMC2 supply voltage (supply voltage for PG[12:9] and PD6 pins)	It can be different from V_{DD}		1.7	-	3.6	

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load).
- All peripherals are disabled except if it is explicitly mentioned.
- The Flash memory access time is adjusted both to f_{HCLK} frequency and V_{DD} range (see *Table 18: Limitations depending on the operating power supply range*).
- When the regulator is ON, the voltage scaling and over-drive mode are adjusted to f_{HCLK} frequency as follows:
  - Scale 3 for $f_{HCLK} \leq 144$ MHz
  - Scale 2 for 144 MHz < $f_{HCLK} \leq 168$ MHz
  - Scale 1 for 168 MHz < $f_{HCLK} \leq 216$ MHz. The over-drive is only ON at 216 MHz.
- When the regulator is OFF, the V12 is provided externally as described in *Table 17: General operating conditions*:
- The system clock is HCLK, $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$.
- External clock frequency is 25 MHz and PLL is ON when f_{HCLK} is higher than 25 MHz.
- The typical current consumption values are obtained for 1.7 V ≤ V_{DD} ≤ 3.6 V voltage range and for T_A= 25 °C unless otherwise specified.
- The maximum values are obtained for 1.7 V ≤ V_{DD} ≤ 3.6 V voltage range and a maximum ambient temperature (T_A) unless otherwise specified.
- For the voltage range 1.7 V ≤ V_{DD} ≤ 3.6 V, the maximum frequency is 180 MHz.

Table 25. Typical and maximum current consumption in Run mode, code with data processing running from ITCM RAM, regulator ON

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in RUN mode	All peripherals enabled(2)(3)	216	156	170(4)	180(4)	200	mA
			200	144	154	164.6	183	
			180	127	134(4)	143(4)	158(4)	
			168	113	119	127.4	141	
			144	86	96	112.6	126	
			60	41	44	52.8	65	
			25	22	24	33.5	45	
		All peripherals disabled(3)	216	99	110(4)	119.6(4)	138.5	
			200	92	102	113.1	132	
			180	81	90(4)	96.7(4)	125(4)	
			168	72	78	86.5	100.1	
			144	55	61	77.1	90.8	
			60	24	25	38.5	50.3	
			25	12	13	26.3	38.1	

1. Guaranteed by characterization results.

Table 38. Low-power mode wakeup timings (continued)

Symbol	Parameter	Conditions	Typ(1)	Max(1)	Unit
t_{WUSTOP}(2)	Wakeup from Stop mode with MR/LP regulator in Under-drive mode	Main regulator in under-drive mode (Flash memory in Deep power-down mode)	107.4	113.2	µs
		Low power regulator in under-drive mode (Flash memory in Deep power-down mode)	112.7	120	
tWUSTDBY(2)	Wakeup from Standby mode	Exit Standby mode on rising edge	308	313	µs
		Exit Standby mode on falling edge	307	313	

1. Guaranteed by characterization results.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first

5.3.9 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the *Table 62: I/O static characteristics*. However, the recommended clock input waveform is shown in *Figure 36*.

The characteristics given in *Table 39* result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 17*.

Table 39. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External user clock source frequency(1)	-	1	-	50	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time(1)		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time(1)		-	-	10	
$C_{in(HSE)}$	OSC_IN input capacitance(1)	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design.

Table 45. Main PLL characteristics (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{LOCK}	PLL lock time	VCO freq = 100 MHz		75	-	200	µs
		VCO freq = 432 MHz		100	-	300	
Jitter(3)	Cycle-to-cycle jitter	System clock 216 MHz	RMS	-	25	-	ps
			peak to peak	-	±150	-	
	Period Jitter		RMS	-	15	-	
			peak to peak	-	±200	-	
	Main clock output (MCO) for RMII Ethernet	Cycle to cycle at 50 MHz on 1000 samples		-	32	-	
	Main clock output (MCO) for MII Ethernet	Cycle to cycle at 25 MHz on 1000 samples		-	40	-	
	Bit Time CAN jitter	Cycle to cycle at 1 MHz on 1000 samples		-	330	-	
$I_{DD(PLL)}$(4)	PLL power consumption on V_{DD}	VCO freq = 100 MHz VCO freq = 432 MHz		0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLL)}$(4)	PLL power consumption on V_{DDA}	VCO freq = 100 MHz VCO freq = 432 MHz		0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between PLL and PLLI2S.
2. Guaranteed by design.
3. The use of 2 PLLs in parallel could degraded the Jitter up to +30%.
4. Guaranteed by characterization results.

Table 46. PLLI2S characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLLI2S_IN}	PLLI2S input clock(1)	-	0.95(2)	1	2.10	MHz
$f_{PLLI2SQ\_OUT}$	PLLI2S multiplier output clock for SAI	-	-	-	216	
$f_{PLLI2SR\_OUT}$	PLLI2S multiplier output clock for I2S	-	-	-	216	
f_{VCO_OUT}	PLLI2S VCO output	-	100	-	432	
t_{LOCK}	PLLI2S lock time	VCO freq = 100 MHz	75	-	200	µs
		VCO freq = 432 MHz	100	-	300	

Table 47. PLLISAI characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$I_{DD(PLLSAI)}$(4)	PLLSAI power consumption on V_{DD}	VCO freq = 100 MHz VCO freq = 432 MHz	0.15 0.45	-	0.40 0.75	mA
$I_{DDA(PLLSAI)}$(4)	PLLSAI power consumption on V_{DDA}	VCO freq = 100 MHz VCO freq = 432 MHz	0.30 0.55	-	0.40 0.85	mA

1. Take care of using the appropriate division factor M to have the specified PLL input clock values.
2. Guaranteed by design.
3. Value given with main PLL running.
4. Guaranteed by characterization results.

5.3.12 PLL spread spectrum clock generation (SSCG) characteristics

The spread spectrum clock generation (SSCG) feature allows to reduce electromagnetic interferences (see *Table 58: EMI characteristics*). It is available only on the main PLL.

Table 48. SSCG parameters constraint

Symbol	Parameter	Min	Typ	Max(1)	Unit
f_{Mod}	Modulation frequency	-	-	10	KHz
md	Peak modulation depth	0.25	-	2	%
MODEPER * INCSTEP	-	-	-	$2^{15} - 1$	-

1. Guaranteed by design.

Equation 1

The frequency modulation period (MODEPER) is given by the equation below:

$$MODEPER = round[f_{PLL\_IN} / (4 \times f_{Mod})]$$

f_{PLL_IN} and f_{Mod} must be expressed in Hz.

As an example:

If f_{PLL_IN} = 1 MHz, and f_{MOD} = 1 kHz, the modulation depth (MODEPER) is given by equation 1:

$$MODEPER = round[10^6 / (4 \times 10^3)] = 250$$

Equation 2

Equation 2 allows to calculate the increment step (INCSTEP):

$$INCSTEP = round[((2^{15} - 1) \times md \times PLLN) / (100 \times 5 \times MODEPER)]$$

f_{VCO_OUT} must be expressed in MHz.

With a modulation depth (md) = ±2 % (4 % peak to peak), and PLLN = 240 (in MHz):

$$INCSTEP = round[((2^{15} - 1) \times 2 \times 240) / (100 \times 5 \times 250)] = 126md(quantitazed)\%$$

Table 68. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{VREF+}(2)	ADC V_{REF} DC current consumption in conversion mode	-	-	300	500	µA
I_{VDDA}(2)	ADC V_{DDA} DC current consumption in conversion mode	-	-	1.6	1.8	mA

1. V_{DDA} minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to *Section 2.17.2: Internal reset OFF*).
2. Guaranteed by characterization results.
3. V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA}.
4. R_{ADC} maximum value is given for V_{DD}=1.7 V, and minimum value for V_{DD}=3.3 V.
5. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 68*.

Equation 1: R_{AIN} max formula

$$R_{AIN} = \frac{(k - 0.5)}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. N = 12 (from 12-bit resolution) and k is the number of sampling periods defined in the ADC_SMPR1 register.

Table 69. ADC static accuracy at f_{ADC} = 18 MHz

Symbol	Parameter	Test conditions	Typ	Max(1)	Unit
ET	Total unadjusted error	f_{ADC} =18 MHz V_{DDA} = 1.7 to 3.6 V V_{REF} = 1.7 to 3.6 V V_{DDA} –V_{REF} < 1.2 V	±3	±4	LSB
EO	Offset error		±2	±3	
EG	Gain error		±1	±3	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±2	±3	

1. Guaranteed by characterization results.

Table 70. ADC static accuracy at f_{ADC} = 30 MHz

Symbol	Parameter	Test conditions	Typ	Max(1)	Unit
ET	Total unadjusted error	f_{ADC} = 30 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 2.4 to 3.6 V, V_{REF} = 1.7 to 3.6 V, V_{DDA} –V_{REF} < 1.2 V	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±4	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±1.5	±3	

1. Guaranteed by characterization results.

Table 90. Dynamic characteristics: USB ULPI(1)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t_{SC}	Control in (ULPI_DIR, ULPI_NXT) setup time	-	1.5	-	-	ns
t_{HC}	Control in (ULPI_DIR, ULPI_NXT) hold time	-	1	-	-	
t_{SD}	Data in setup time	-	1.5	-	-	
t_{HD}	Data in hold time	-	1	-	-	
t_{DC}/t_{DD}	Data/control output delay	2.7 V < V_{DD} < 3.6 V, C_L = 20 pF and OSPEEDRy[1:0] = 11	-	6	7.5	
		-	-	9.5	11	
		1.7 V < V_{DD} < 3.6 V, C_L = 15 pF and OSPEEDRy[1:0] = 11	-			

1. Guaranteed by characterization results.

USB high speed (HS) characteristics (Embedded PHY High speed in STM32F723xx devices)

Table 91. USB OTG high speed DC electrical characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{hssq}	High speed squelch detection threshold	-	100	-	150	mV
V_{hsdsc}	High speed disconnect detection threshold	-	525	-	625	mV
V_{hsdif}	High speed differential detection threshold	-	100	-	-	mV
V_{hscm}	High speed data signalling common mode voltage range	-	-50	-	500	mV
V_{hsoi}	High speed idle level	-	-10	-	10	mV
V_{hsoh}	High speed data signaling high	-	360	-	440	mV
V_{hsol}	High speed data signaling low	-	-10	-	10	mV
V_{chirpj}	Chirp J level	-	700	-	1100	mV
V_{chirpk}	Chirp K level	-	-900	-	-500	mV

Table 92. USB OTG high speed electrical characteristics

Parameter	Comments	Conditions	Min	Typ	Max	Unit
t_{lr}	Rise time	-	0.5	-	-	ns
t_{lf}	Fall time	-	0.5	-	-	ns
t_{lrfm}	Setup time from INHSDRIVERENABLE=1 to the transition on INHSDATAP/INHSDATAN	-	10	-	-	ns
Z_{drv}	Driver output impedance	-	40.5	-	49.5	Ω

1. Guaranteed by characterization results.

Table 101. Asynchronous multiplexed PSRAM/NOR write-NWAIT timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	9Thclk - 1	9Thclk + 1	ns
$t_{w(NWE)}$	FMC_NWE low time	7Thclk -0.5	7Thclk + 0.5	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	6Thclk + 2	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	4Thclk - 1	-	

1. Guaranteed by characterization results.

Synchronous waveforms and timings

Figure 65 through *Figure 68* represent synchronous waveforms and *Table 102* through *Table 105* provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- BurstAccessMode = FMC_BurstAccessMode_Enable;
- MemoryType = FMC_MemoryType_CRAM;
- WriteBurst = FMC_WriteBurst_Enable;
- CLKDivision = 1;
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM
- CL = 30 pF on data and address lines. CL = 10 pF on FMC_CLK unless otherwise specified.

In all timing tables, the T_{HCLK} is the HCLK clock period.

– For 2.7 V≤V_{DD}≤3.6 V, maximum FMC_CLK = 108 MHz at CL=20 pF or 90 MHz at CL=30 pF (on FMC_CLK).

– For 1.71 V≤V_{DD}<2.7 V, maximum FMC_CLK = 70 MHz at CL=10 pF (on FMC_CLK).

Figure 65. Synchronous multiplexed NOR/PSRAM read timings

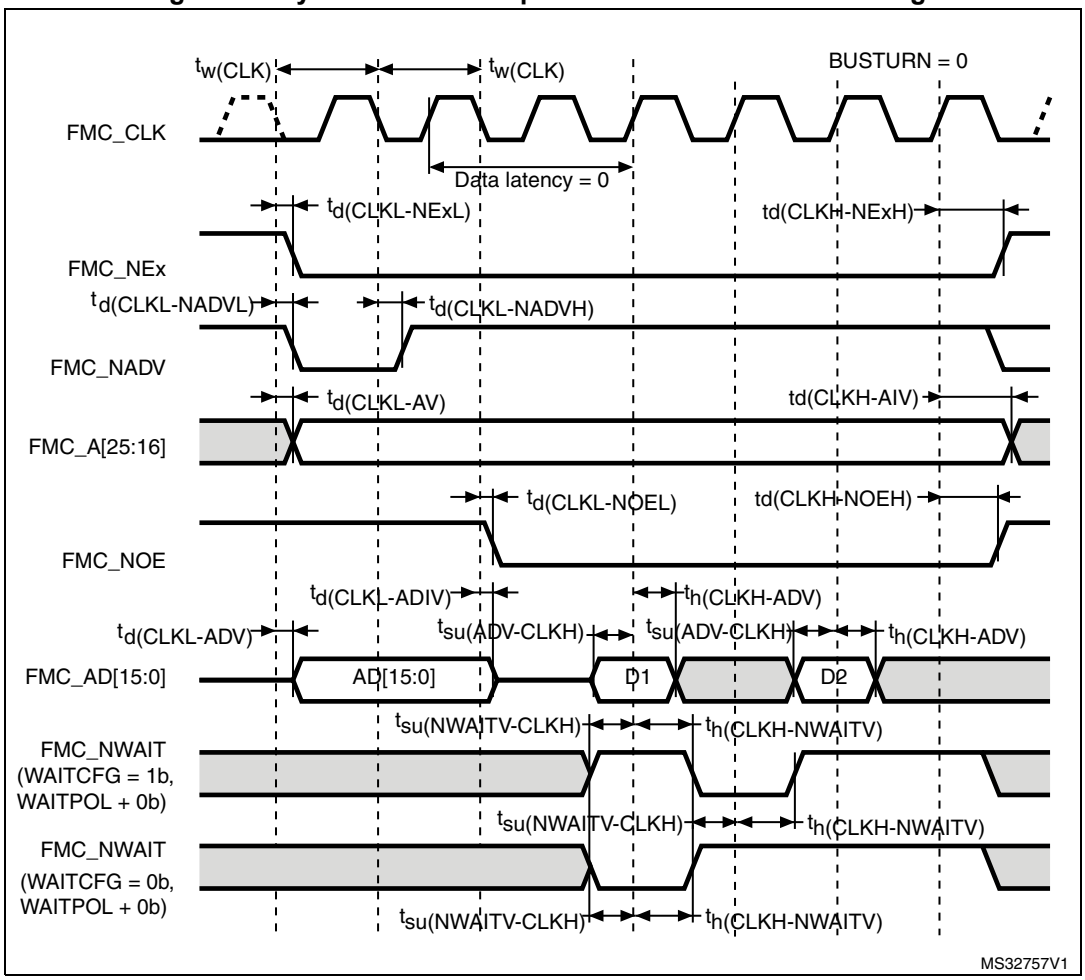


Table 105. Synchronous non-multiplexed PSRAM write timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{(CLK)}$	FMC_CLK period	2Thclk - 0.5	-	ns
$t_{d(CLKL-NExL)}$	FMC_CLK low to FMC_NEx low (x=0..2)	-	2	
$t_{(CLKH-NExH)}$	FMC_CLK high to FMC_NEx high (x= 0…2)	Thclk +0.5	-	
$t_{d(CLKL-NADVL)}$	FMC_CLK low to FMC_NADV low	-	0.5	
$t_{d(CLKL-NADVH)}$	FMC_CLK low to FMC_NADV high	0	-	
$t_{d(CLKL-AV)}$	FMC_CLK low to FMC_Ax valid (x=16…25)	-	3	
$t_{d(CLKH-AIV)}$	FMC_CLK high to FMC_Ax invalid (x=16…25)	Thclk	-	
$t_{d(CLKL-NWEL)}$	FMC_CLK low to FMC_NWE low	-	1.5	
$t_{d(CLKH-NWEH)}$	FMC_CLK high to FMC_NWE high	Thclk +1	-	
$t_{d(CLKL-Data)}$	FMC_D[15:0] valid data after FMC_CLK low	-	3	
$t_{d(CLKL-NBLL)}$	FMC_CLK low to FMC_NBL low	-	2	
$t_{d(CLKH-NBLH)}$	FMC_CLK high to FMC_NBL high	Thclk +1	-	
$t_{su(NWAIT-CLKH)}$	FMC_NWAIT valid before FMC_CLK high	2	-	
$t_{h(CLKH-NWAIT)}$	FMC_NWAIT valid after FMC_CLK high	3.5	-	

1. Guaranteed by characterization results.

NAND controller waveforms and timings

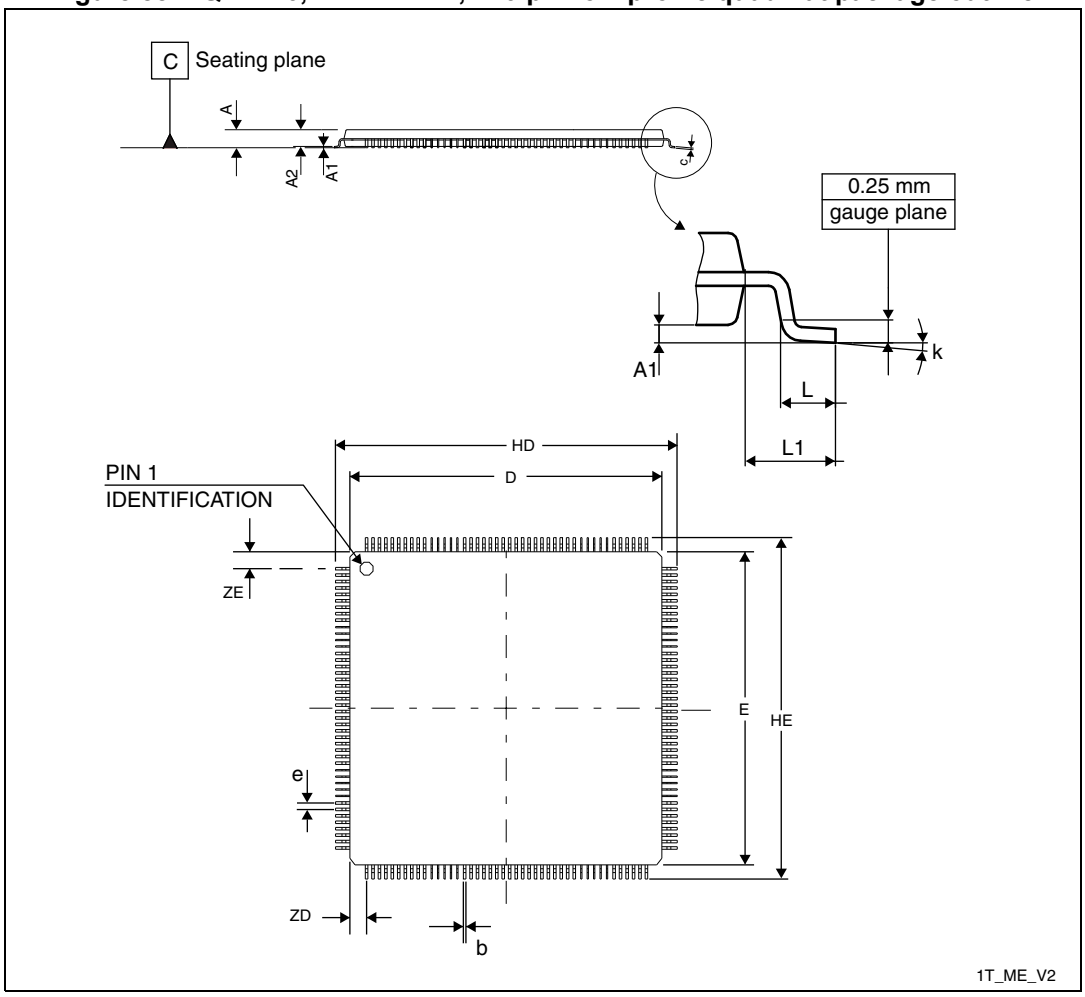
Figure 69 through *Figure 72* represent synchronous waveforms, and *Table 106* and *Table 107* provide the corresponding timings. The results shown in this table are obtained with the following FMC configuration:

- COM.FMC_SetupTime = 0x01;
- COM.FMC_WaitSetupTime = 0x03;
- COM.FMC_HoldSetupTime = 0x02;
- COM.FMC_HiZSetupTime = 0x01;
- ATT.FMC_SetupTime = 0x01;
- ATT.FMC_WaitSetupTime = 0x03;
- ATT.FMC_HoldSetupTime = 0x02;
- ATT.FMC_HiZSetupTime = 0x01;
- Bank = FMC_Bank_NAND;
- MemoryDataWidth = FMC_MemoryDataWidth_16b;
- ECC = FMC_ECC_Enable;
- ECCPageSize = FMC_ECCPageSize_512Bytes;
- TCLRSetupTime = 0;
- TARSetupTime = 0.

In all timing tables, the T_{HCLK} is the HCLK clock period.

6.4 LQFP176 24 x 24 mm low-profile quad flat package information

Figure 88. LQFP176, 24 x 24 mm, 176-pin low-profile quad flat package outline



1. Drawing is not to scale.

Table 119. LQFP176, 24 x 24 mm, 176-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	-	1.450	0.0531	-	0.0060
b	0.170	-	0.270	0.0067	-	0.0106
C	0.090	-	0.200	0.0035	-	0.0079
D	23.900	-	24.100	0.9409	-	0.9488